

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-11 (canceled).

12. (new) A semiconductor light-emitting device comprising an elongated light transmitter, a pair of metallic heat sinks disposed on opposite ends of the transmitter, a semiconductor light-emitting element mounted on each of said heat sinks toward the transmitter for emitting a light which is introduced into the transmitter from the both ends thereof to radiate light outside from an outer peripheral surface of the transmitter, and a plastic encapsulant formed with an annular groove to envelop main and side surfaces of the heat sink by said plastic encapsulant, wherein each of said heat sinks comprises a reflector integrally formed with or secured on a main surface of the heat sink,

said reflector has a flaring inner surface which gradually expands toward the transmitter to surround said semiconductor light-emitting element,

said transmitter is formed of transparent or translucent glass or resin into a hollow or solid cylindrical shape, and

each end of said transmitter is fitted into said annular groove to join each end of the transmitter to the reflector.

13. (new) The semiconductor light-emitting device of claim 12, further comprises a light reflective film formed on at least a portion of outer or inner peripheral surface of the transmitter.

14. (new) The semiconductor light-emitting device of claim 12, further comprises a lens portion covering upper surface of the reflector,

wherein light from said semiconductor light-emitting element is reflected on the inner surface of the reflector and introduced through the lens portion into the transmitter.

15. (new) The semiconductor light-emitting device of claim 12, wherein said reflector 5 is formed of an electrically conductive metallic material,

a lead wire passes through a notch of the reflector to electrically connect the semiconductor light-emitting element and an outer lead.

16. (new) A method for producing a semiconductor light-emitting device, comprising the steps of:

disposing a pair of heat sinks on opposite ends of a transmitter, each of said heat sinks comprising a reflector integrally formed with or secured on a main surface of heat sink,

securing a semiconductor light-emitting element on a main surface of each heat sink within said reflector which gradually expands toward upside,

electrically connecting an electrode on said semiconductor light-emitting element and an outer lead through a lead wire,

forming a plastic encapsulant with an annular groove to envelop the main and side surfaces of the heat sink, a side surface of the reflector and an inner end of the outer lead by said plastic encapsulant, and

fitting each end of an elongated light transmitter into said annular groove to join each end of the transmitter to the reflector.

17. (new) A linear light source comprising an elongated light transmitter which has an irradiation surface and two ends, a semiconductor light-emitting element for emitting light introduced into said light transmitter from each of two ends thereof, a plurality of half-mirrors provided in said light transmitter for reflecting light introduced into said light transmitter from light-emitting element out of said light transmitter through the irradiation surface, and at least one total reflection mirror provided inside said half-mirrors in the light transmitter,

wherein said total reflection mirror reflects light permeated through said half-mirrors toward the outside of said light transmitter through said irradiation surface.

18. (new) The linear light source of claim 17, wherein a plurality of said half-mirrors are provided in said light transmitter, said half-mirrors being across and inclined at a certain angle to a longitudinal central line of said light transmitter.

19. (new) The linear light source of claim 17, wherein said half-mirrors have the lower light-reflectivity and the higher light permeability, the closer said half-mirrors are disposed to the semiconductor light-emitting element.

20. (new) The linear light source of claim 17, wherein said half-mirror formed into a plate shape is sandwiched between a plurality of segments of said light transmitter.

21. (new) The linear light source of claim 17, wherein said half-mirrors are formed by vapor deposition on at least one

inclined surface of plural segments of said light transmitter,
and said inclined surfaces of plural segments are in contact to
each other.